

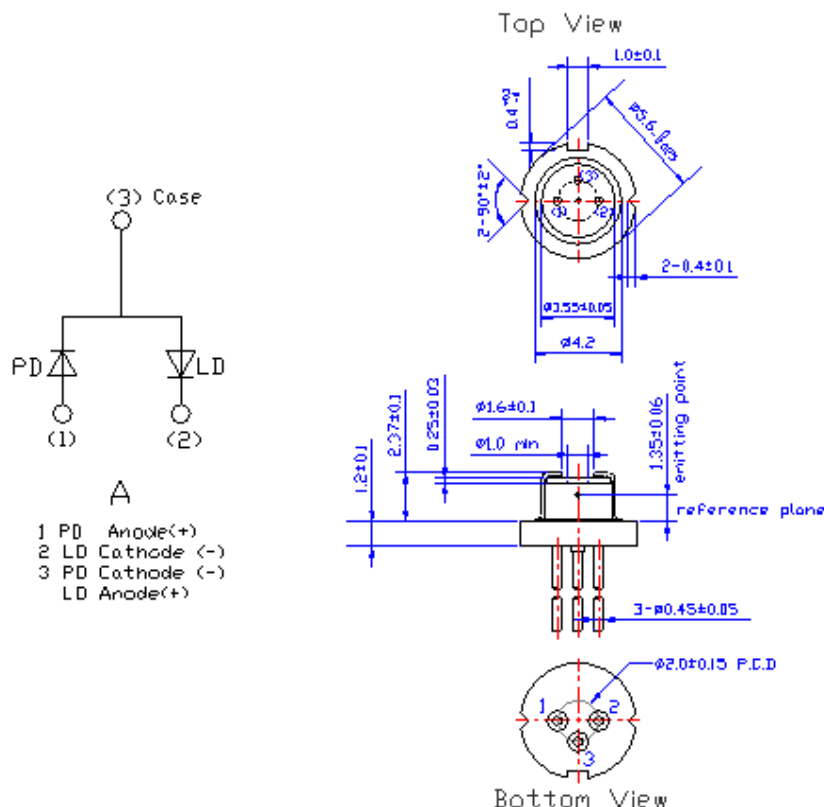
660nm Red Laser Diode NEW66A051A-preliminary



Specifications

- (1) Device: Laser Diode
- (2) Structure: TO-18(ψ 5.6mm), With Pb free glass cap, PD

External dimensions(Unit : mm)



Absolute Maximum Ratings($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Optical Output	Po	100	mW
Reverse Voltage	Laser	Vr	2 V
	PIN PD	Vr(PIN)	30 V
Operating Temperature	Top	-10~+50	°C
Storage Temperature	Tstg	-40~+85	°C

660nm Laser Diode**■ Electrical and Optical Characteristics(Tc=25°C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Threshold Current	I _{th}	P _o =100mW	-	80	90	mA	
Operating Current	I _{op}	P _o =100mW	-	190	210	mA	
Operating Voltage	V _{op}	-	-	2.3	2.5	Volts	
Slope Efficiency	η	75mW-25mW	0.5	0.85	-	mW	
		I _{75mW} -I _{25mW}				mA	
Monitor Current	I _m	P _o =100mW	-	0.1	1.0	mA	
Beam Divergence (FWHM)	Parallel	$\theta //$	P _o =100mW	5	11	17	deg.
	Perpendicular	$\theta \perp$	P _o =100mW	10	27	34	deg.
Lasing Wavelength	λ	P _o =100mW	655	660	665	nm	

◎ $\theta //$ and $\theta \perp$ are defined as the angle within which the intensity is 50% of the peak value.